

80V/2.5A Peak, High Frequency Full Bridge FET Driver

November 1996

Features

- Independently Drives 4 N-Channel FET in Half Bridge or Full Bridge Configurations
- Bootstrap Supply Max Voltage to 95V_{DC}
- Drives 1000pF Load at 1MHz in Free Air at 50°C with Rise and Fall Times of Typically 10ns
- User-Programmable Dead Time
- On-Chip Charge-Pump and Bootstrap Upper Bias Supplies
- DIS (Disable) Overrides Input Control
- Input Logic Thresholds Compatible with 5V to 15V Logic Levels
- Very Low Power Consumption
- Undervoltage Protection

Applications

- Medium/Large Voice Coil Motors
- Full Bridge Power Supplies
- Class D Audio Power Amplifiers
- High Performance Motor Controls
- Noise Cancellation Systems
- · Battery Powered Vehicles
- Peripherals
- U.P.S.

Description

The HIP4081A is a high frequency, medium voltage Full Bridge N-Channel FET driver IC, available in 20 lead plastic SOIC and DIP packages. The HIP4081A can drive every possible switch combination except those which would cause a shoot-through condition. The HIP4081A can switch at frequencies up to 1MHz and is well suited to driving Voice Coil Motors, high-frequency Class D audio amplifiers, and power supplies.

For example, the HIP4081A can drive medium voltage brush motors, and two HIP4081As can be used to drive high performance stepper motors, since the short minimum "on-time" can provide fine micro-stepping capability.

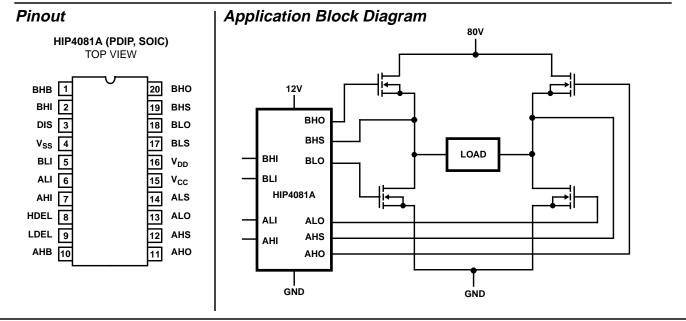
Short propagation delays of approximately 55ns maximizes control loop crossover frequencies and dead-times which can be adjusted to near zero to minimize distortion, resulting in rapid, precise control of the driven load.

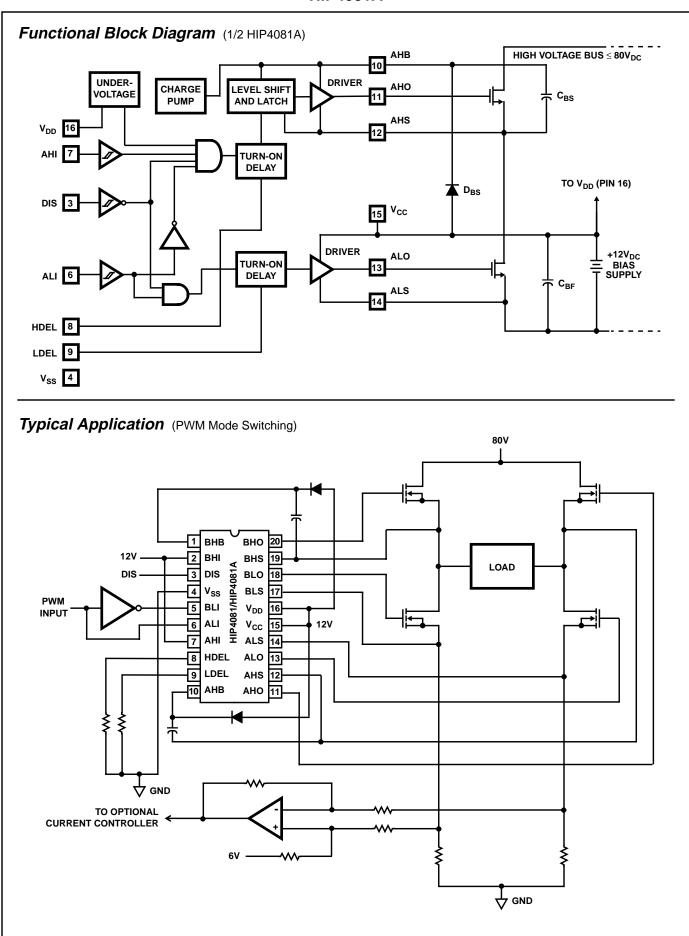
A similar part, the HIP4080A, includes an on-chip input comparator to create a PWM signal from an external triangle wave and to facilitate "hysteresis mode" switching.

The Application Note for the HIP4081A is the AN9405.

Ordering Information

PART NUMBER	TEMP RANGE (°C)	PACKAGE	PKG. NO.
HIP4081AIP	-40 to 85	20 Ld PDIP	E20.3
HIP4081AIB	-40 to 85	20 Ld SOIC (W)	M20.3





Absolute Maximum Ratings

Supply Voltage, V_{DD} and $\mathrm{V}_{\mathrm{CC}}.$ -0.3V to 16V Logic I/O Voltages -0.3V to V_{DD} +0.3V Voltage on AHS, BHS....-6.0V (Transient) to 80V (25°C to 125°C)

Voltage on AHS, BHS... -6.0V (Transient) to 70V (-55°C to 125°C) Voltage on ALS, BLS-2.0V (Transient) to +2.0V (Transient) Voltage on AHB, BHB $V_{AHS, BHS}$ -0.3V to $V_{AHS, BHS}$ + V_{DD} Voltage on ALO, BLO $V_{ALS, BLS}$ -0.3V to V_{CC} +0.3V Voltage on AHO, BHO $V_{AHS, BHS}$ -0.3V to $V_{AHB, BHB}$ +0.3V

Input Current, HDEL and LDEL -5mA to 0mA NOTE: All Voltages relative to V_{SS} , unless otherwise specified.

Thermal Information

Thermal Resistance (Typical, Note 1)	θ _{JA} (°C/W)
SOIC Package	. 85
DIP Package	
Storage Temperature Range	-65°C to 150°C
Operating Max. Junction Temperature	125°C
Lead Temperature (Soldering 10s))	300°C
(For SOIC - Lead Tips Only	

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

1. θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

Operating Conditions

Supply Voltage, $V_{\mbox{\scriptsize DD}}$ and $V_{\mbox{\scriptsize CC}}.$ +9.5V to +15V Voltage on ALS, BLS -1.0V to +1.0V Operating Ambient Temperature Range -40°C to 85°C Voltage on AHB, BHB.....V_{AHS, BHS} +5V to V_{AHS, BHS} +15V

			1	Γ _J = 25°(C	T _{JS} = -40°C TO 125°C		
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	MIN	MAX	UNITS
SUPPLY CURRENTS AND CHA	RGE PUMPS							
V _{DD} Quiescent Current	I _{DD}	All inputs = 0V	8.5	10.5	14.5	7.5	14.5	mA
V _{DD} Operating Current	I _{DDO}	Outputs switching f = 500kHz	9.5	12.5	15.5	8.5	15.5	mA
V _{CC} Quiescent Current	I _{CC}	All Inputs = 0V, $I_{ALO} = I_{BLO} = 0$	-	0.1	10	-	20	μΑ
V _{CC} Operating Current	I _{cco}	f = 500kHz, No Load	1	1.25	2.0	0.8	3	mA
AHB, BHB Quiescent Current - Qpump Output Current	I _{AHB} , I _{BHB}	All Inputs = 0V, $I_{AHO} = I_{BHO} = 0$ $V_{DD} = V_{CC} = V_{AHB} = V_{BHB} = 10V$	-50	-30	-11	-60	-10	μΑ
AHB, BHB Operating Current	І _{АНВО} , І _{ВНВО}	f = 500kHz, No Load	0.6	1.2	1.5	0.5	1.9	mA
AHS, BHS, AHB, BHB Leakage Current	I _{HLK}	$V_{BHS} = V_{AHS} = 80V,$ $V_{AHB} = V_{BHB} = 93V$	-	0.02	1.0	-	10	μΑ
AHB-AHS, BHB-BHS Qpump Output Voltage	V _{AHB} -V _{AHS} V _{BHB} -V _{BHS}	$I_{AHB} = I_{AHB} = 0$, No Load	11.5	12.6	14.0	10.5	14.5	V
INPUT PINS: ALI, BLI, AHI, BH	, AND DIS							
Low Level Input Voltage	V _{IL}	Full Operating Conditions	-	-	1.0	-	0.8	V
High Level Input Voltage	V _{IH}	Full Operating Conditions	2.5	-	-	2.7	-	V
Input Voltage Hysteresis			-	35	-	-	-	mV
Low Level Input Current	I _{IL}	V _{IN} = 0V, Full Operating Conditions	-130	-100	-75	-135	-65	μΑ
High Level Input Current	I _{IH}	V _{IN} = 5V, Full Operating Conditions	-1	-	+1	-10	+10	μΑ
TURN-ON DELAY PINS: LDEL	AND HDEL							
LDEL, HDEL Voltage	V_{HDEL} , V_{LDEL}	I _{HDEL} = I _{LDEL} = -100μA	4.9	5.1	5.3	4.8	5.4	V
GATE DRIVER OUTPUT PINS:	ALO, BLO, AH	O, AND BHO						
Low Level Output Voltage	V _{OL}	I _{OUT} = 100mA	0.7	0.85	1.0	0.5	1.1	V
High Level Output Voltage	V _{CC} -V _{OH}	I _{OUT} = -100mA	0.8	0.95	1.1	0.5	1.2	V
Peak Pullup Current	I _O +	V _{OUT} = 0V	1.7	2.6	3.8	1.4	4.1	Α
Peak Pulldown Current	I ₀ -	V _{OUT} = 12V	1.7	2.4	3.3	1.3	3.6	Α

			T _J = 25°C		T _{JS} = -40°C TO 125°C			
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	MIN	MAX	UNITS
Undervoltage, Rising Threshold	UV+		8.1	8.8	9.4	8.0	9.5	V
Undervoltage, Falling Threshold	UV-		7.6	8.3	8.9	7.5	9.0	V
Undervoltage, Hysteresis	HYS		0.25	0.4	0.65	0.2	0.7	V

Switching Specifications $V_{DD} = V_{CC} = V_{AHB} = V_{BHB} = 12V$, $V_{SS} = V_{ALS} = V_{BLS} = V_{AHS} = 0V$, $V_{BHS} = 0V$, $V_{BHS} = 10V$, $V_{CL} = 1000$ pF.

			T _J = 25°C			-40°C 25°C		
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	MIN	MAX	UNITS
Lower Turn-off Propagation Delay (ALI-ALO, BLI-BLO)	T _{LPHL}		-	30	60	-	80	ns
Upper Turn-off Propagation Delay (AHI-AHO, BHI-BHO)	T _{HPHL}		-	35	70	-	90	ns
Lower Turn-on Propagation Delay (ALI-ALO, BLI-BLO)	T _{LPLH}	R _{HDEL} = R _{LDEL} = 10K	-	45	70	-	90	ns
Upper Turn-on Propagation Delay (AHI-AHO, BHI-BHO)	T _{HPLH}	R _{HDEL} = R _{LDEL} = 10K	-	60	90	-	110	ns
Rise Time	T _R		-	10	25	-	35	ns
Fall Time	T _F		-	10	25	-	35	ns
Turn-on Input Pulse Width	T _{PWIN-ON}	R _{HDEL} = R _{LDEL} = 10K	50	-	-	50	-	ns
Turn-off Input Pulse Width	T _{PWIN-OFF}	R _{HDEL} = R _{LDEL} = 10K	40	-	-	40	-	ns
Turn-on Output Pulse Width	T _{PWOUT-ON}	R _{HDEL} = R _{LDEL} = 10K	40	-	-	40	-	ns
Turn-off Output Pulse Width	T _{PWOUT-OFF}	R _{HDEL} = R _{LDEL} = 10K	30	-	-	30	-	ns
Disable Turn-off Propagation Delay (DIS - Lower Outputs)	T _{DISLOW}		-	45	75	-	95	ns
Disable Turn-off Propagation Delay (DIS - Upper Outputs)	T _{DISHIGH}		-	55	85	-	105	ns
Disable to Lower Turn-on Propagation Delay (DIS - ALO and BLO)	T _{DLPLH}		-	40	70	-	90	ns
Refresh Pulse Width (ALO and BLO)	T _{REF-PW}		240	410	550	200	600	ns
Disable to Upper Enable (DIS - AHO and BHO)	T _{UEN}		-	450	620	-	690	ns

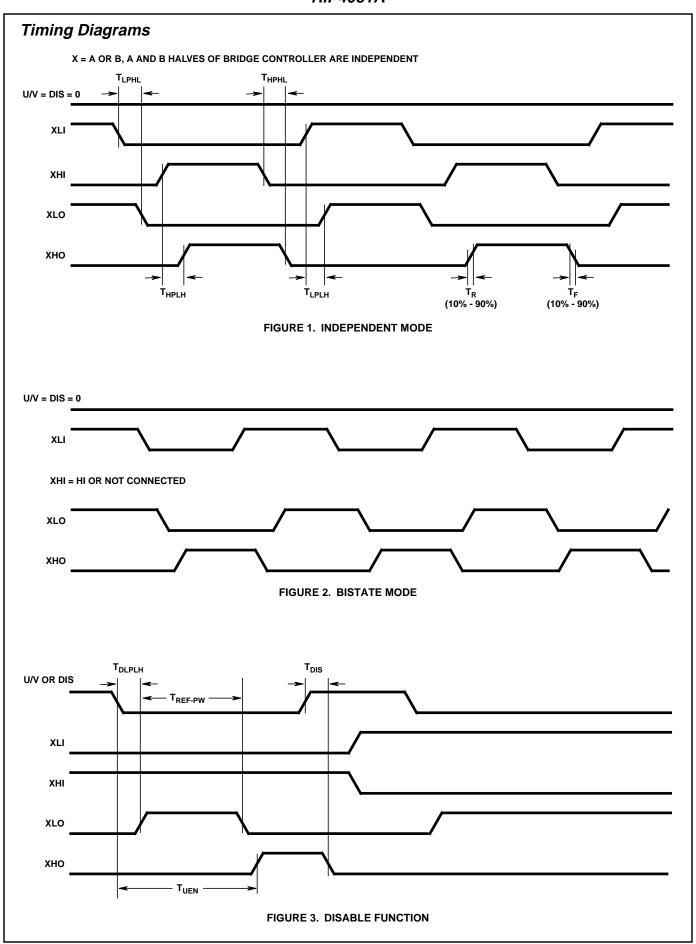
TRUTH TABLE

	INF	ОИТРИТ			
ALI, BLI	AHI, BHI	U/V	DIS	ALO, BLO	АНО, ВНО
X	Х	Х	1	0	0
1	Х	0	0	1	0
0	1	0	0	0	1
0	0	0	0	0	0
Х	Х	1	Х	0	0

NOTE: X signifies that input can be either a "1" or "0".

Pin Descriptions

PIN NUMBER	SYMBOL	DESCRIPTION
1	ВНВ	B High-side Bootstrap supply. External bootstrap diode and capacitor are required. Connect cathode of bootstrap diode and positive side of bootstrap capacitor to this pin. Internal charge pump supplies 30μA out of this pin to maintain bootstrap supply. Internal circuitry clamps the bootstrap supply to approximately 12.8V.
2	ВНІ	B High-side Input. Logic level input that controls BHO driver (Pin 20). BLI (Pin 5) high level input overrides BHI high level input to prevent half-bridge shoot-through, see Truth Table. DIS (Pin 3) high level input overrides BHI high level input. The pin can be driven by signal levels of 0V to 15V (no greater than V_{DD}). An internal 100 μ A pull-up to V_{DD} will hold BHI high, so no connection is required if high-side and low-side outputs are to be controlled by the low-side input.
3	DIS	DISable input. Logic level input that when taken high sets all four outputs low. DIS high overrides all other inputs. When DIS is taken low the outputs are controlled by the other inputs. The pin can be driven by signal levels of 0V to 15V (no greater than V_{DD}). An internal 100 μ A pull-up to V_{DD} will hold DIS high if this pin is not driven.
4	V _{SS}	Chip negative supply, generally will be ground.
5	BLI	B Low-side Input. Logic level input that controls BLO driver (Pin 18). If BHI (Pin 2) is driven high or not connected externally then BLI controls both BLO and BHO drivers, with dead time set by delay currents at HDEL and LDEL (Pin 8 and 9). DIS (Pin 3) high level input overrides BLI high level input. The pin can be driven by signal levels of 0V to 15V (no greater than V _{DD}). An internal 100μA pull-up to V _{DD} will hold BLI high if this pin is not driven.
6	ALI	A Low-side Input. Logic level input that controls ALO driver (Pin 13). If AHI (Pin 7) is driven high or not connected externally then ALI controls both ALO and AHO drivers, with dead time set by delay currents at HDEL and LDEL (Pin 8 and 9). DIS (Pin 3) high level input overrides ALI high level input. The pin can be driven by signal levels of 0V to 15V (no greater than V _{DD}). An internal 100μA pull-up to V _{DD} will hold ALI high if this pin is not driven.
7	АНІ	A High-side Input. Logic level input that controls AHO driver (Pin 11). ALI (Pin 6) high level input overrides AHI high level input to prevent half-bridge shoot-through, see Truth Table. DIS (Pin 3) high level input overrides AHI high level input. The pin can be driven by signal levels of 0V to 15V (no greater than V_{DD}). An internal 100 μ A pull-up to V_{DD} will hold AHI high, so no connection is required if high-side and low-side outputs are to be controlled by the low-side input.
8	HDEL	High-side turn-on DELay. Connect resistor from this pin to V _{SS} to set timing current that defines the turn-on delay of both high-side drivers. The low-side drivers turn-off with no adjustable delay, so the HDEL resistor guarantees no shoot-through by delaying the turn-on of the high-side drivers. HDEL reference voltage is approximately 5.1V.
9	LDEL	Low-side turn-on DELay. Connect resistor from this pin to V _{SS} to set timing current that defines the turn-on delay of both low-side drivers. The high-side drivers turn-off with no adjustable delay, so the LDEL resistor guarantees no shoot-through by delaying the turn-on of the low-side drivers. LDEL reference voltage is approximately 5.1V.
10	AHB	A High-side Bootstrap supply. External bootstrap diode and capacitor are required. Connect cathode of bootstrap diode and positive side of bootstrap capacitor to this pin. Internal charge pump supplies 30μA out of this pin to maintain bootstrap supply. Internal circuitry clamps the bootstrap supply to approximately 12.8V.
11	AHO	A High-side Output. Connect to gate of A High-side power MOSFET.
12	AHS	A High-side Source connection. Connect to source of A High-side power MOSFET. Connect negative side of bootstrap capacitor to this pin.
13	ALO	A Low-side Output. Connect to gate of A Low-side power MOSFET.
14	ALS	A Low-side Source connection. Connect to source of A Low-side power MOSFET.
15	V _{CC}	Positive supply to gate drivers. Must be same potential as V_{DD} (Pin 16). Connect to anodes of two bootstrap diodes.
16	V_{DD}	Positive supply to lower gate drivers. Must be same potential as V _{CC} (Pin 15). De-couple this pin to V _{SS} (Pin 4).
17	BLS	B Low-side Source connection. Connect to source of B Low-side power MOSFET.
18	BLO	B Low-side Output. Connect to gate of B Low-side power MOSFET.
19	BHS	B High-side Source connection. Connect to source of B High-side power MOSFET. Connect negative side of bootstrap capacitor to this pin.
20	вно	B High-side Output. Connect to gate of B High-side power MOSFET.



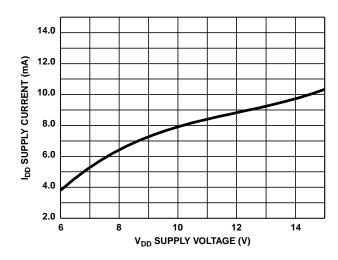


FIGURE 4. QUIESCENT I_{DD} SUPPLY CURRENT vs V_{DD} SUPPLY VOLTAGE

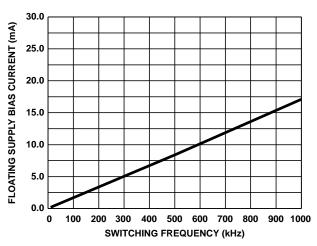


FIGURE 6. SIDE A, B FLOATING SUPPLY BIAS CURRENT vs FREQUENCY (LOAD = 1000pF)

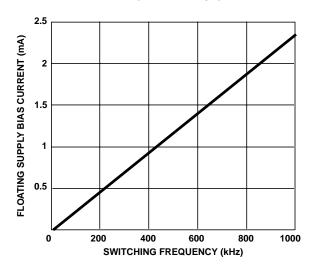


FIGURE 8. I_{AHB} , I_{BHB} , NO-LOAD FLOATING SUPPLY BIAS CURRENT vs FREQUENCY

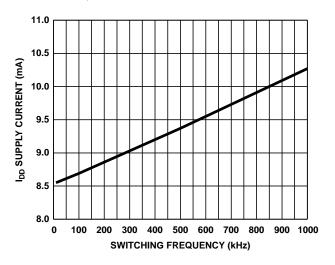


FIGURE 5. I_{DDO} , NO-LOAD I_{DD} SUPPLY CURRENT vs FREQUENCY (kHz)

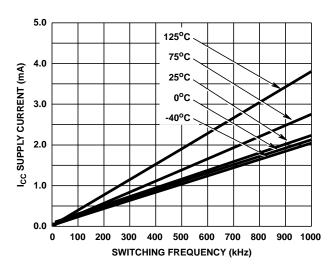


FIGURE 7. I_{CCO} , NO-LOAD I_{CC} SUPPLY CURRENT vs FREQUENCY (kHz) TEMPERATURE

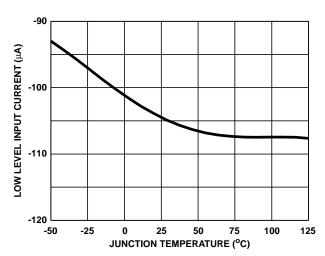
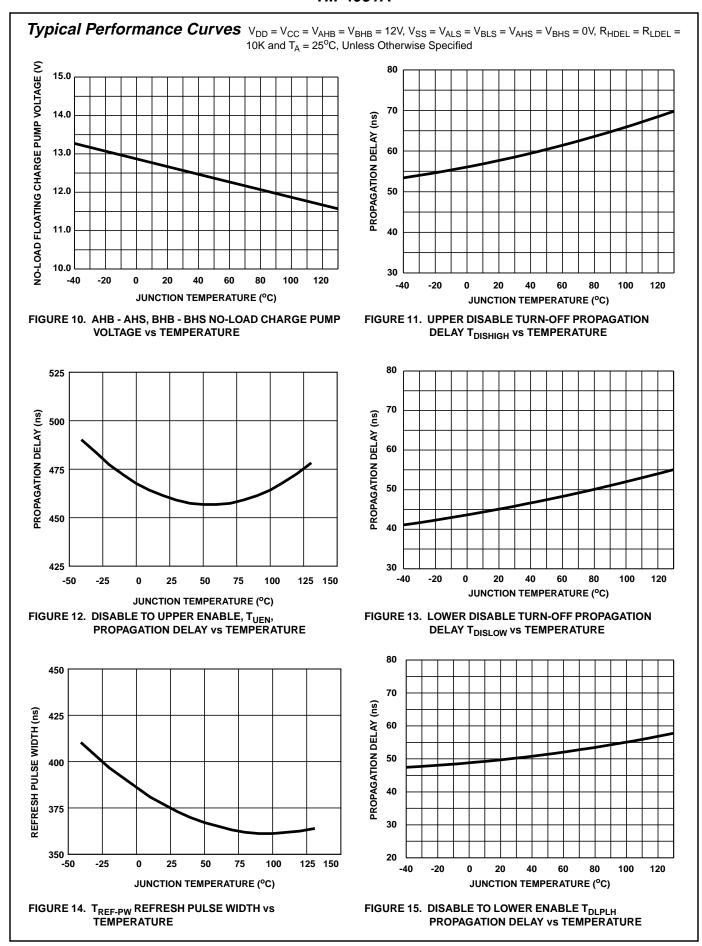
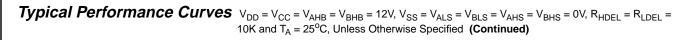
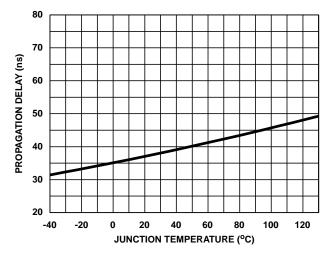


FIGURE 9. ALI, BLI, AHI, BHI LOW LEVEL INPUT CURRENT $I_{\rm IL}$ vs TEMPERATURE







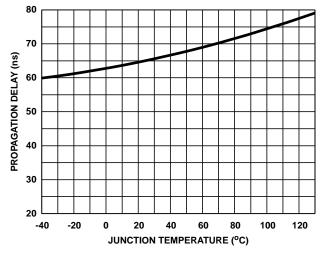
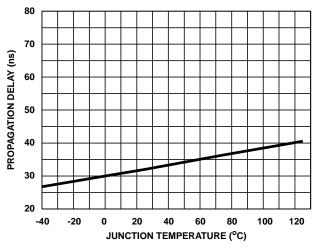


FIGURE 16. UPPER TURN-OFF PROPAGATION DELAY $T_{\mbox{\scriptsize HPHL}}$ vs $T_{\mbox{\scriptsize EMPERATURE}}$

FIGURE 17. UPPER TURN-ON PROPAGATION DELAY T_{HPLH} vs $T_{EMPERATURE}$



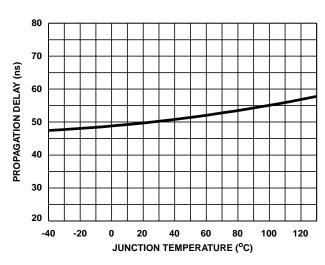
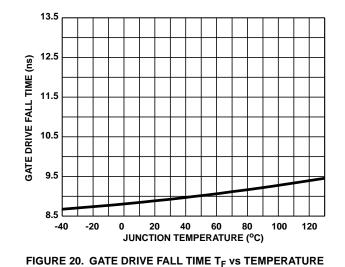


FIGURE 18. LOWER TURN-OFF PROPAGATION DELAY T_{LPHL} vs TEMPERATURE

FIGURE 19. LOWER TURN-ON PROPAGATION DELAY T_{LPLH} vs T_{LPLH} vs



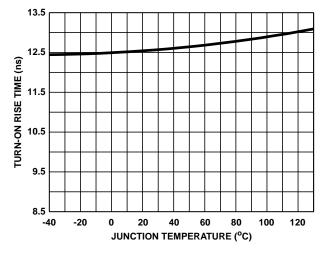
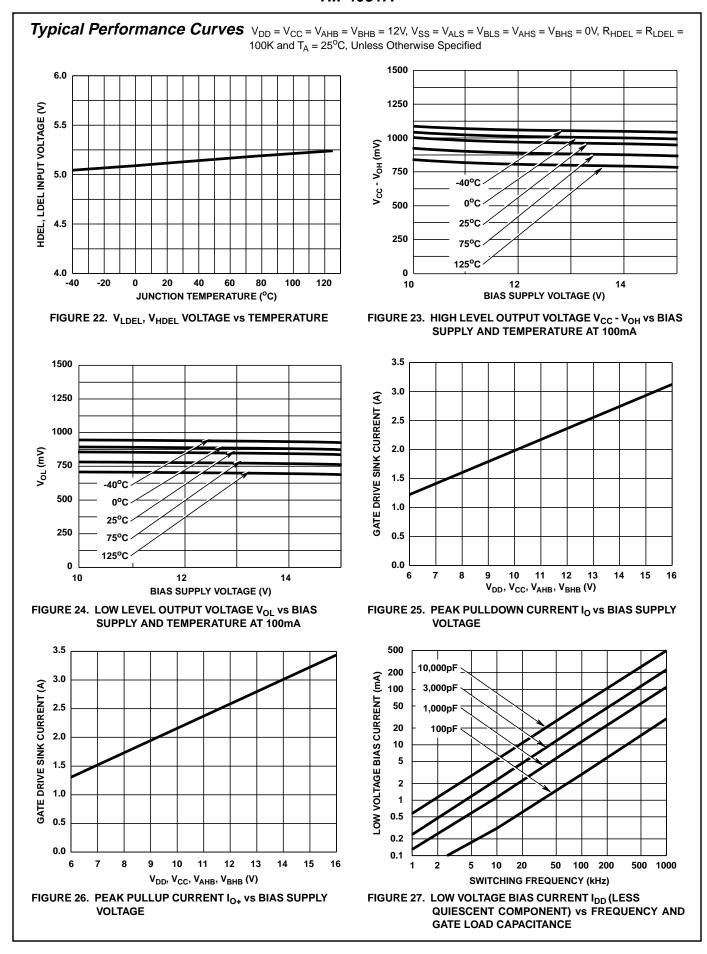


FIGURE 21. GATE DRIVE RISE TIME T_R vs TEMPERATURE



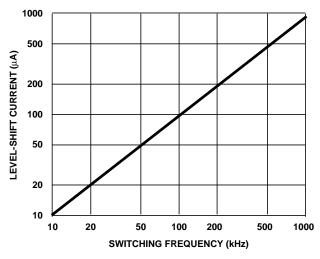


FIGURE 28. HIGH VOLTAGE LEVEL-SHIFT CURRENT vs FREQUENCY AND BUS VOLTAGE

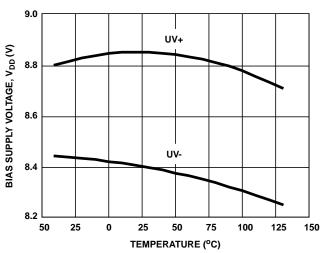


FIGURE 29. UNDERVOLTAGE LOCKOUT vs TEMPERATURE

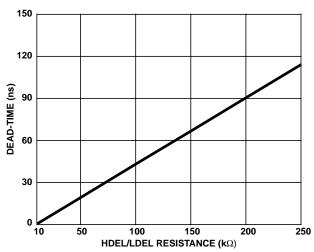
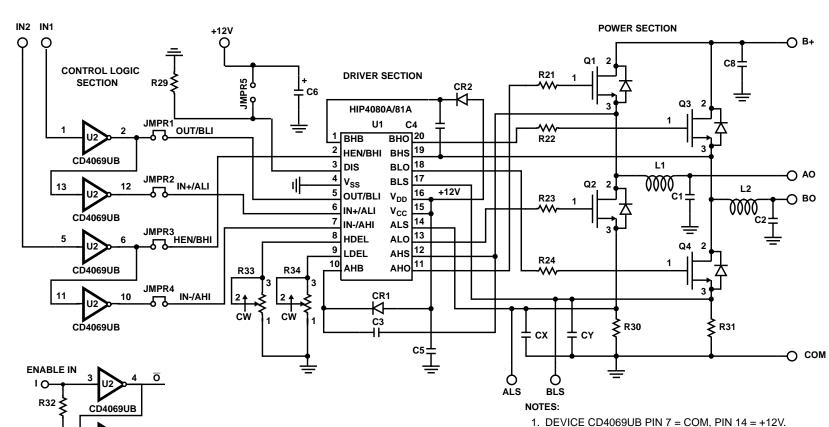


FIGURE 30. MINIMUM DEAD-TIME vs DEL RESISTANCE



- 2. COMPONENTS L1, L2, C1, C2, CX, CY, R30, R31, NOT SUPPLIED. REFER TO APPLICATION NOTE FOR DESCRIPTION OF INPUT LOGIC OPERATION TO DETERMINE JUMPER LOCATIONS FOR JMPR1 - JMPR4.

FIGURE 31. HIP4081A EVALUATION PC BOARD SCHEMATIC

CD4069UB

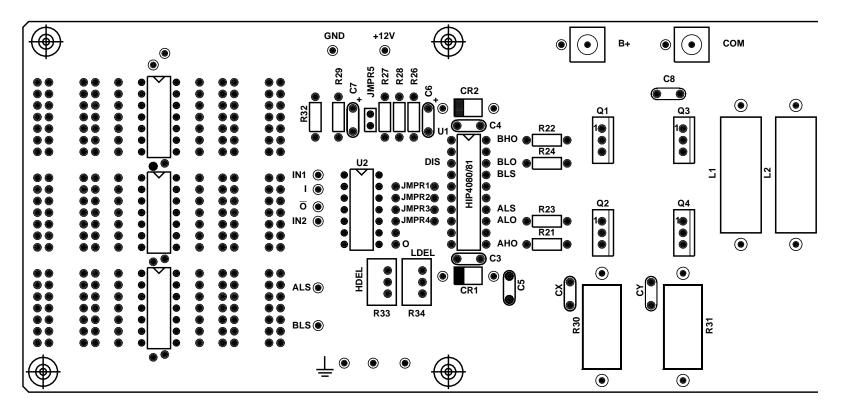
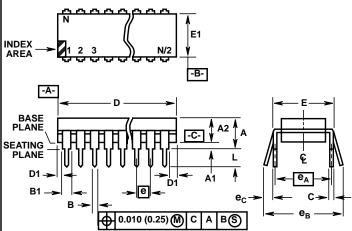


FIGURE 32. HIP4081A EVALUATION BOARD SILKSCREEN

Dual-In-Line Plastic Packages (PDIP)



NOTES:

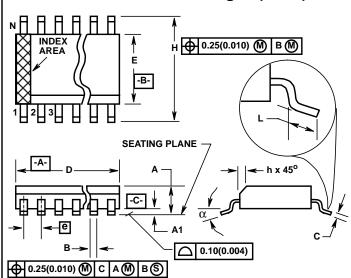
- Controlling Dimensions: INCH. In case of conflict between English and Metric dimensions, the inch dimensions control.
- 2. Dimensioning and tolerancing per ANSI Y14.5M-1982.
- 3. Symbols are defined in the "MO Series Symbol List" in Section 2.2 of Publication No. 95.
- 4. Dimensions A, A1 and L are measured with the package seated in JEDEC seating plane gauge GS-3.
- D, D1, and E1 dimensions do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.010 inch (0.25mm).
- E and e_A are measured with the leads constrained to be perpendicular to datum -C-.
- 7. e_B and e_C are measured at the lead tips with the leads unconstrained. e_C must be zero or greater.
- 8. B1 maximum dimensions do not include dambar protrusions. Dambar protrusions shall not exceed 0.010 inch (0.25mm).
- 9. N is the maximum number of terminal positions.
- Corner leads (1, N, N/2 and N/2 + 1) for E8.3, E16.3, E18.3, E28.3, E42.6 will have a B1 dimension of 0.030 - 0.045 inch (0.76 - 1.14mm).

E20.3 (JEDEC MS-001-AD ISSUE D) 20 LEAD DUAL-IN-LINE PLASTIC PACKAGE

	INC	HES	MILLIM		
SYMBOL	MIN	MAX	MIN	MAX	NOTES
Α	-	0.210	-	5.33	4
A1	0.015	-	0.39	-	4
A2	0.115	0.195	2.93	4.95	-
В	0.014	0.022	0.356	0.558	-
B1	0.045	0.070	1.55	1.77	8
С	0.008	0.014	0.204	0.355	-
. D	0.980	1.060	24.89	26.9	5
D1	0.005	-	0.13	-	5
Е	0.300	0.325	7.62	8.25	6
E1	0.240	0.280	6.10	7.11	5
е	0.100	BSC	2.54	BSC	-
e _A	0.300	BSC	7.62 BSC		6
e _B	-	0.430	-	10.92	7
L	0.115	0.150	2.93	3.81	4
N	2	0	2	9	

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Small Outline Plastic Packages (SOIC)



M20.3 (JEDEC MS-013-AC ISSUE C) 20 LEAD WIDE BODY SMALL OUTLINE PLASTIC PACKAGE

	INC	HES	MILLIM		
SYMBOL	MIN	MAX	MIN	MAX	NOTES
Α	0.0926	0.1043	2.35	2.65	-
A1	0.0040	0.0118	0.10	0.30	-
В	0.013	0.0200	0.33	0.51	9
С	0.0091	0.0125	0.23	0.32	-
D	0.4961	0.5118	12.60	13.00	3
Е	0.2914	0.2992	7.40	7.60	4
е	0.050	BSC	1.27	BSC	-
Н	0.394	0.419	10.00	10.65	-
h	0.010	0.029	0.25	0.75	5
L	0.016	0.050	0.40	1.27	6
N	2	0	20		7
α	0°	8º	0°	8°	-

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NOTES:

- Symbols are defined in the "MO Series Symbol List" in Section 2.2 of Publication Number 95.
- 2. Dimensioning and tolerancing per ANSI Y14.5M-1982.
- Dimension "D" does not include mold flash, protrusions or gate burrs. Mold flash, protrusion and gate burrs shall not exceed 0.15mm (0.006 inch) per side.
- Dimension "E" does not include interlead flash or protrusions. Interlead flash and protrusions shall not exceed 0.25mm (0.010 inch) per side.
- 5. The chamfer on the body is optional. If it is not present, a visual index feature must be located within the crosshatched area.
- 6. "L" is the length of terminal for soldering to a substrate.
- 7. "N" is the number of terminal positions.
- 8. Terminal numbers are shown for reference only.
- The lead width "B", as measured 0.36mm (0.014 inch) or greater above the seating plane, shall not exceed a maximum value of 0.61mm (0.024 inch)
- Controlling dimension: MILLIMETER. Converted inch dimensions are not necessarily exact.

All Intersil semiconductor products are manufactured, assembled and tested under ISO9000 quality systems certification.

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